

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



December 2012

FDP8441

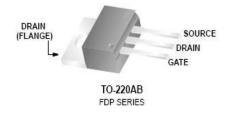
N-Channel PowerTrench® MOSFET 40V, 80A, 2.7m Ω

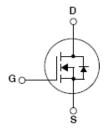
Features

- Typ $r_{DS(on)} = 2.1 m\Omega$ at $V_{GS} = 10 V$, $I_D = 80 A$
- Typ $Q_{g(10)} = 215nC$ at $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- RoHS Compliant

Applications

- Solenoid and Motor Drivers
- Distributed Power Architectures and VRMs





$\textbf{MOSFET Maximum Ratings} \ \, \textbf{T}_{C} = 25^{\circ} \text{C unless otherwise noted}$

| Symbol | Parameter | Ratings | Units | |
|-----------------------------------|--|---------|--------------|------|
| V_{DS} | Drain to Source Voltage | 40 | V | |
| V_{GS} | Gate to Source Voltage | | ±20 | V |
| | Drain Current Continuous (T _C < 160°C, V _{GS} = 10V) | | | |
| I _D | Continuous ($T_{amb} = 25^{\circ}C$, $V_{GS} = 10V$, with $R_{\theta JA} = 62^{\circ}C/W$) | | 23 | Α |
| | Pulsed | | See Figure 4 | |
| E _{AS} | Single Pulse Avalanche Energy (| Note 1) | 947 | mJ |
| c | Power dissipation | | 300 | W |
| P_{D} | Derate above 25°C | | 2 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature | | -55 to 175 | °C |

Thermal Characteristics

| $R_{\theta JC}$ | R _{0JC} Thermal Resistance Junction to Case | | 0.5 | °C/W |
|-----------------|--|----------|-----|------|
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient | (Note 2) | 62 | °C/W |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|---------|----------|-----------|------------|----------|
| FDP8441 | FDP8441 | TO-220AB | Tube | N/A | 50 units |

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units | l |
|------------|------------|-----------------|-----|-----|-----|-------|---|
| | | | | | | | |
| Off Charac | cteristics | | | | | | |

| B _{VDSS} | Drain to Source Breakdown Voltage | $I_D = 250 \mu A, V_{GS} = 0 V$ | | 40 | - | - | V |
|------------------------------|-----------------------------------|---------------------------------|----------------------|----|---|------|----|
| | Zero Gate Voltage Drain Current | $V_{DS} = 32V$ | | - | - | 1 | ^ |
| IDSS Zero Gate Voltage Drain | Zero Gate Voltage Drain Current | $V_{GS} = 0V$ | $T_J = 150^{\circ}C$ | - | - | 250 | μΑ |
| I _{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20V$ | | - | - | ±100 | nA |

On Characteristics

| V_{G} | S(th) | Gate to Source Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 2 | 2.8 | 4 | V |
|-----------------|-------|----------------------------------|--|---|-----|-----|----|
| | | | $I_D = 80A, V_{GS} = 10V$ | - | 2.1 | 2.7 | |
| r _{DS} | G(on) | Drain to Source On Resistance | $I_D = 80A, V_{GS} = 10V,$ $T_J = 175^{\circ}C$ | - | 3.6 | 4.7 | mΩ |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V 05V V 0V | | - | 15000 | = | pF |
|------------------|----------------------------------|------------------------------------|----------------------------------|---|-------|-----|----|
| C _{oss} | Output Capacitance | $V_{DS} = 25V, V_{GS}$ f = 1MHz | $V_{DS} = 25V, V_{GS} = 0V,$ | | 1250 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 - 11VII 12 | | - | 685 | - | pF |
| R_{G} | Gate Resistance | $V_{GS} = 0.5V, f = 1$ | V _{GS} = 0.5V, f = 1MHz | | 1.1 | - | Ω |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V | V _{GS} = 0 to 10V | | - | 215 | 280 | nC |
| $Q_{g(TH)}$ | Threshold Gate Charge | $V_{GS} = 0$ to $2V$ | $V_{DD} = 20V$ | - | 29 | 38 | nC |
| Q_{gs} | Gate to Source Gate Charge | | $I_{D} = 35A$ | - | 60 | - | nC |
| Q _{gs2} | Gate Charge Threshold to Plateau | $I_g = 1mA$ | | - | 32 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | - | 49 | - | nC |

Electrical Characteristics $T_J = 25^{\circ}\text{C}$ unless otherwise noted

| Symbol Parameter | Test Conditions | Min | Тур | Max | Units |
|------------------|-----------------|-----|-----|-----|-------|
|------------------|-----------------|-----|-----|-----|-------|

Switching Characteristics

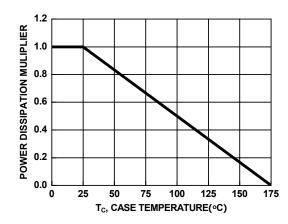
| t _(on) | Turn-On Time | | - | - | 77 | ns |
|---------------------|---------------------|------------------------------------|---|------|-----|----|
| t _{d(on)} | Turn-On Delay Time | | - | 23 | - | ns |
| t _r | Turn-On Rise Time | $V_{DD} = 20V, I_{D} = 35A$ | - | 24 | - | ns |
| t _{d(off)} | Turn-Off Delay Time | $V_{GS} = 10V, R_{GS} = 1.5\Omega$ | | 75 | - | ns |
| t _f | Turn-Off Fall Time | | - | 17.9 | - | ns |
| t _{off} | Turn-Off Time | | - | - | 147 | ns |

Drain-Source Diode Characteristics

| V _{SD} | Source to Drain Diode Voltage | I _{SD} = 35A | - | 0.8 | 1.25 | V |
|-----------------|-------------------------------|-------------------------------------|---|-----|------|----|
| | Source to Drain Diode Voltage | I _{SD} = 15A | - | 0.8 | 1.0 | V |
| t _{rr} | Reverse Recovery Time | $I_F = 35A$, di/dt = 100A/ μ s | - | 52 | 68 | ns |
| Q _{rr} | Reverse Recovery Charge | $I_F = 35A$, di/dt = 100A/ μ s | - | 76 | 99 | nC |

Notes: 1: Starting $T_J=25^{\circ}C$, L=0.46mH, $I_{AS}=64A$. 2: Pulse width = 100s.

Typical Characteristics



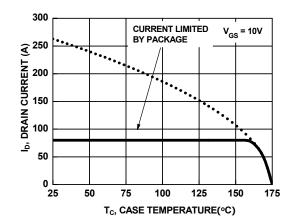


Figure 1. Normalized Power Dissipation vs Case Temperature

Figure 2. Maximum Continuous Drain Current vs Case Temperature

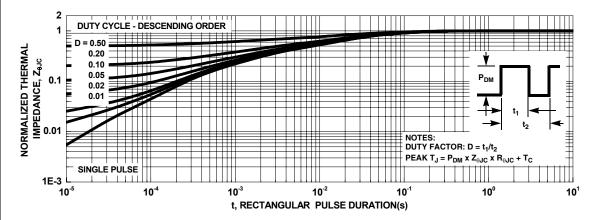


Figure 3. Normalized Maximum Transient Thermal Impedance

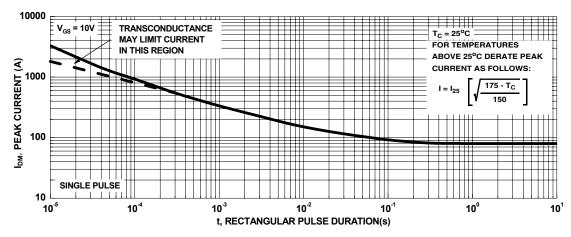


Figure 4. Peak Current Capability

Typical Characteristics

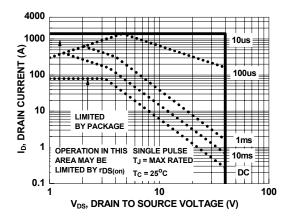
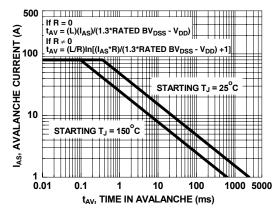


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

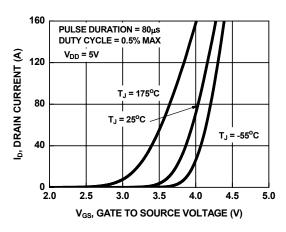


Figure 7. Transfer Characteristics

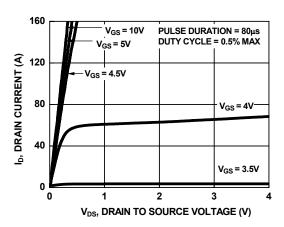


Figure 8. Saturation Characteristics

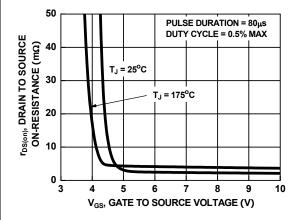


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

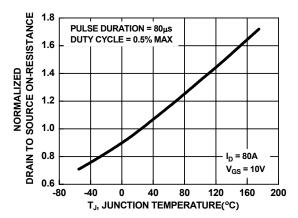


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

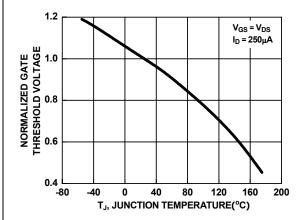


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

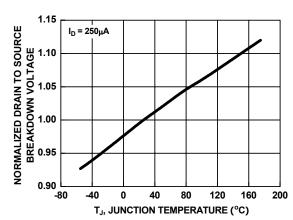


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

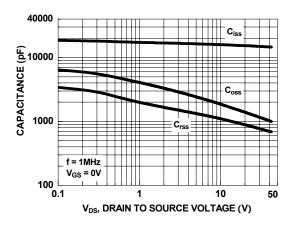


Figure 13. Capacitance vs Drain to Source Voltage

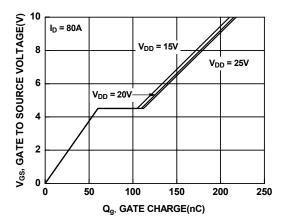


Figure 14. Gate Charge vs Gate to Source Voltage





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAP™* BitSiC® Build it Now™ CorePLUS™

CorePOWER™ CROSSVOLT™ Current Transfer Logic™ DEUXPEED®

Dual Cool™ EcoSPARK® EfficentMax™ ESBC™

Fairchild® Fairchild Semiconductor®

FACT Quiet Series™ FACT $\widetilde{\mathsf{FAST}^{\mathbb{R}}}$ FastvCore[™] FFTBench™ FlashWriter® *

F-PFS™ FRFET®

Global Power ResourceSM Green Bridge™ Green FPS™

Green FPS™ e-Series™ $\mathsf{G} max^\mathsf{TM}$ $\mathsf{GTO^{\mathsf{TM}}}$ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder and Better[™] MegaBuck™

MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ Motion-SPM™

mWSaver™ OptoHiT™ OPTOLOGIC® OPTOPLANAR® PowerTrench® PowerXSTM

Programmable Active Droop™

QFET® QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™ SPM®

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS®

Sync-Lock™ SYSTEM ®* GENERAL

SyncFET™

The Power Franchise®

bwer franchise TinyBoost™ TinyBuck™ TinyCalc™ TinyLogic[®] TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC® TriFault Detect™ TRUECURRENT®* μSerDes™

UHC® Ultra FRFET™ UniFET™ VCX^{TM} VisualMax™ VoltagePlus™ XS^{TM}

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN, NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS **Definition of Terms**

| Datasheet Identification Product Status | | Definition |
|---|-------------------|---|
| Advance Information Formative / In Design | | Datasheet contains the design specifications for product development. Specifications may change in any manner without notice. |
| Preliminary | First Production | Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| No Identification Needed | Full Production | Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design. |
| Obsolete | Not In Production | Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only. |

Rev. 161

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and h

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative